MSKSEMI 美森科















1N4448W

Product specification





FEATURES

- Small Package
- Low Reverse Current
- Fast Switching Speed
- Surface Mount Package Ideally Suited for Automatic Insertion

Reference News

PACKAGE OUTLINE		MARKING	
	o——————————	T5	
S	DD-123		

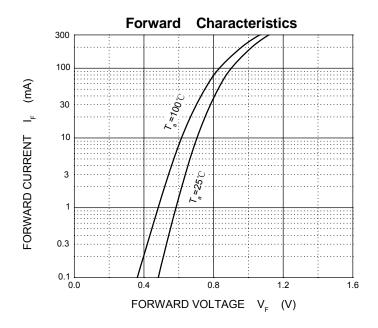
Maximum Ratings and Electrical Characteristics, Single Diode @Ta=25 $^{\circ}$ C

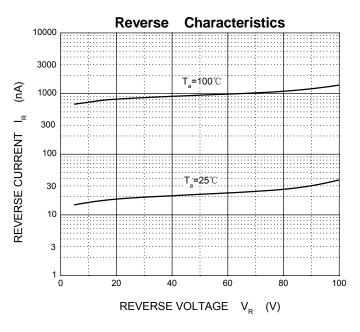
Parameter	Symbol	Limit	Unit
Non-Repetitive Peak Reverse Voltage	V _{RM}	100	V
Peak Repetitive Peak Reverse Voltage	V _{RRM}		
Working Peak Reverse Voltage	V_{RWM}	75	V
DC Blocking Voltage	VR		
RMS Reverse Voltage	V _{R(RMS)}	53	V
Forward Continuous Current	I _{FM}	500	mA
Average Rectified Output Current	lo	250	mA
Non-Repetitive Peak Forward Surge Current @t=8.3ms	I _{FSM}	2.0	А
Power Dissipation	Pd	500	mW
Thermal Resistance Junction to Ambient	ReJA	250	°C/W
Operation Junction and Storage Temperature Range	T _J ,T _{STG}	-55~+150	°C

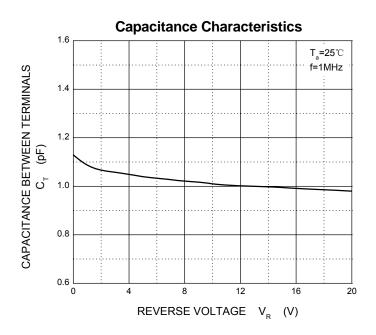
Electrical Ratings @Ta=25℃

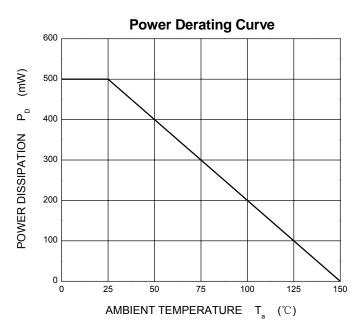
Parameter	Symbol	Min	Тур	Max	Unit	Conditions
Reverse Breakdown Voltage	V (BR)R	75			V	l≈=10µA
	V _{F1}	0.62		0.72	V	l⊧=5mA
Forward Voltage	V _{F2}			0.855	V	l⊧=10mA
I of ward Voltage	V _{F3}			1.0	V	l=100mA
	V _{F4}			1.25	V	⊫=150mA
Reverse Current	I _{R1}			2.5	μA	V _R =75V
Reverse Current	I _{R2}			25	nA	V _R =20V
Capacitance Between Terminals	Ст			4	pF	V _R =0V,f=1MHz
Reverse Recovery Time	trr			4	ns	l⊧=I _R =10mA Irr=0.1XI _R ,R _L =100Ω





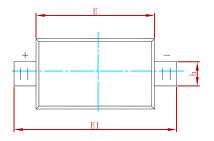


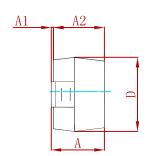


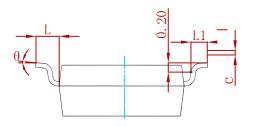




PACKAGE MECHANICAL DATA

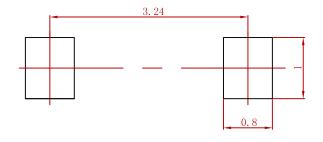






Symbol	Dimensions	In Millimeters	Dimensions In Inches		
	Min	Max	Min	Max	
Α	1.050	1.250	0.041	0.049	
A1	0.000	0.100	0.000	0.004	
A2	1.050	1.150	0.041	0.045	
b	0.450	0.650	0.018	0.026	
С	0.080	0.150	0.003	0.006	
D	1.500	1.700	0.059	0.067	
Е	2.600	2.800	0.102	0.110	
E1	3.550	3.850	0.140	0.152	
Ĺ	0.500 REF		0.020 REF		
L1	0.250	0.450	0.010	0.018	
θ	0°	8°	0°	8°	

Suggested Pad Layout



Note:

- 1.Controllng dlmenslon:in mlllmeters. 2.General tolerance:± 0.05mm.
- 3. The pad layout Is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
1N4448W	SOD-123	3000



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